VBL1208N Datasheet

N-Channel 200 V (D-S) 175 °C MOSFET

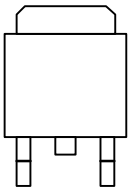
PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
200	0.048 at V_{GS} = 10 V	40
	0.060 at V_{GS} = 6.5 V	35

FEATURES

- Trench Power MOSFET
- 175 °C Junction Temperature
- Low Thermal Resistance Package
- PWM Optimized for Fast Switching
- Compliant to RoHS Directive 2002/95/EC

RoHS COMPLIANT

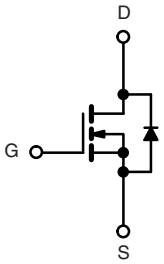
TO-263



Top View

APPLICATIONS

- Isolated DC/DC Converters
  - Primary-Side Switch



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	200	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 175 °C)	T_C = 25 °C	I_D	40	A
	T_C = 125 °C		25	
Pulsed Drain Current		I_{DM}	80	
Avalanche Current		I_{AR}	20	
Repetitive Avalanche Energy[a]	L = 0.1 mH	E_{AR}	16.2	mJ
Maximum Power Dissipation[a]	T_C = 25 °C	P_D	200[b]	W
	T_A = 25 °C[c]		4.5	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Limit	Unit
Junction-to-Ambient	PCB Mount (TO-263)[c]	R_{thJA}	40	°C/W
Junction-to-Case (Drain)		R_{thJC}	1	

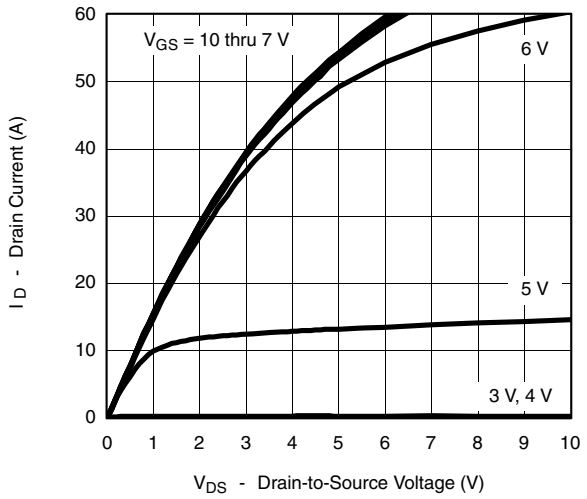
Notes:
a. Duty cycle ≤ 1 %.
b. See SOA curve for voltage derating.
c. When mounted on 1" square PCB (FR-4 material).

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min .**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	200			V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	2		4	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 160 V, V_{GS} = 0 V			1	µA
		V_{DS} = 160 V, V_{GS} = 0 V, T_J = 125 °C			50	
		V_{DS} = 160 V, V_{GS} = 0 V, T_J = 175 °C			250	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 15 V, V_{GS} = 10 V	60			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 20 A		0.048		Ω
		V_{GS} = 10 V, I_D = 20 A, T_J = 125 °C		0.150		
		V_{GS} = 10 V, I_D = 20 A, T_J = 175 °C		0.180		
Drain-Source on State Resistance		V_{GS}= 6.5 V, I_D = 15 A		0.060		
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 30 A	15			S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		2820		pF
Output Capacitance	C_{oss}			300		
Reverse Transfer Capacitance	C_{rss}			120		
Total Gate Charge[c]	Q_g	V_{DS} = 100 V, V_{GS} = 10 V, I_D = 20 A		35		nC
Gate-Source Charge[c]	Q_{gs}			11		
Gate-Drain Charge[c]	Q_{gd}			14		
Gate Resistance	R_G			2		Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 100 V, R_L = 5 Ω I_D ≅ 20 A, V_{GEN} = 10 V, R_G = 2.5 Ω		15	25	ns
Rise Time[c]	t_r			35	55	
Turn-Off Delay Time[c]	$t_{d(off)}$			40	60	
Fall Time[c]	t_f			30	45	
Source-Drain Diode Ratings and Characteristics (T_C = 25 °C)[b]						
Continuous Current	I_S				40	A
Pulsed Current	I_{SM}				60	
Forward Voltage[a]	V_{SD}	I_F = 20 A, V_{GS} = 0 V		1	1.5	V
Reverse Recovery Time	t_{rr}	I_F = 50 A, dI/dt = 100 A/µs		115	170	ns
Peak Reverse Recovery Charge	$I_{RM(REC)}$			7.5	12	A
Reverse Recovery Charge	Q_{rr}			0.43	1.02	µC

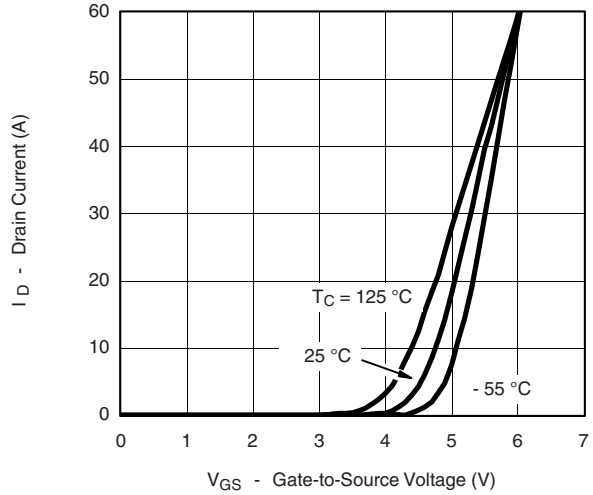
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

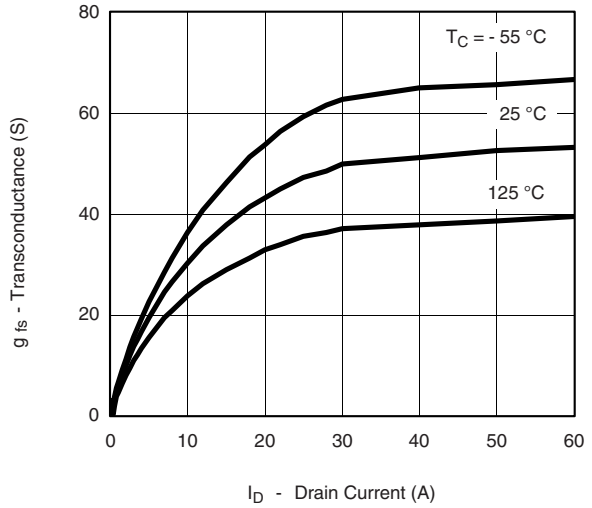
TYPICAL CHARACTERISTICS (25 °C unless noted)



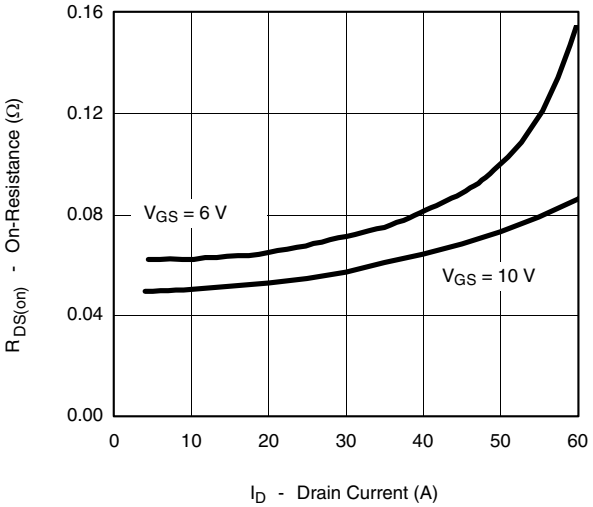
Output Characteristics



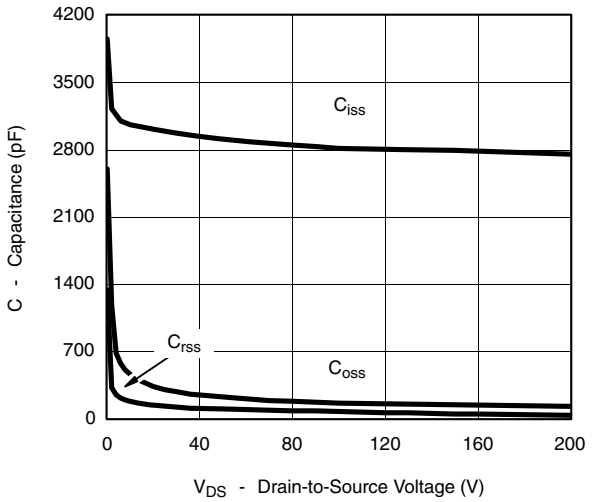
Transfer Characteristics



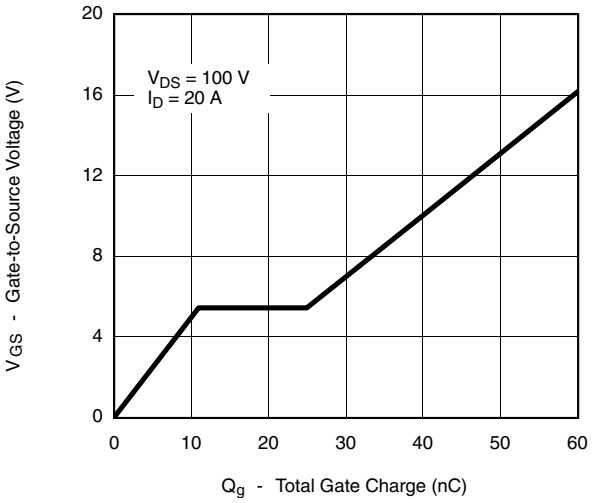
Transconductance



On-Resistance vs. Drain Current

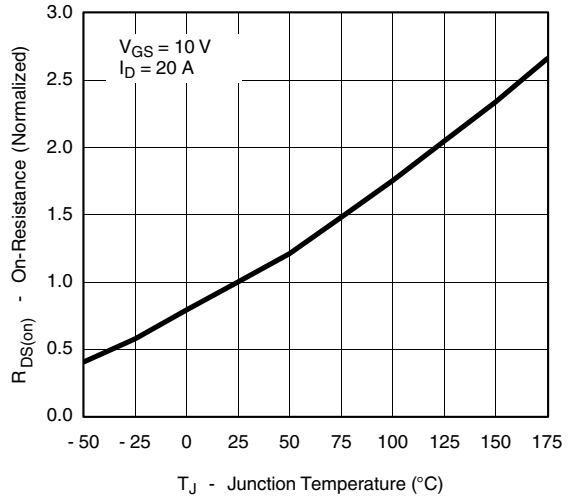


Capacitance

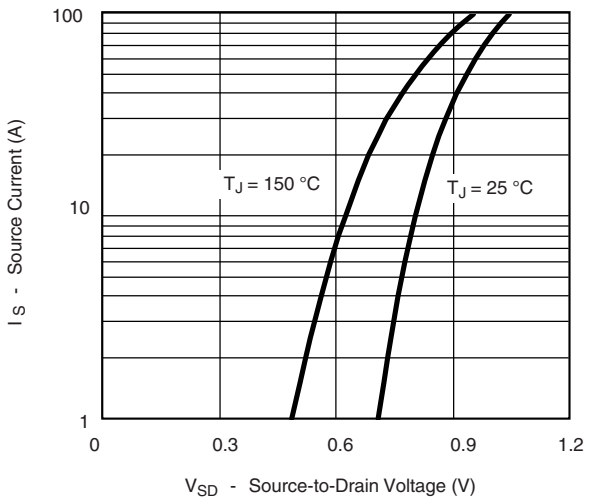


Gate Charge

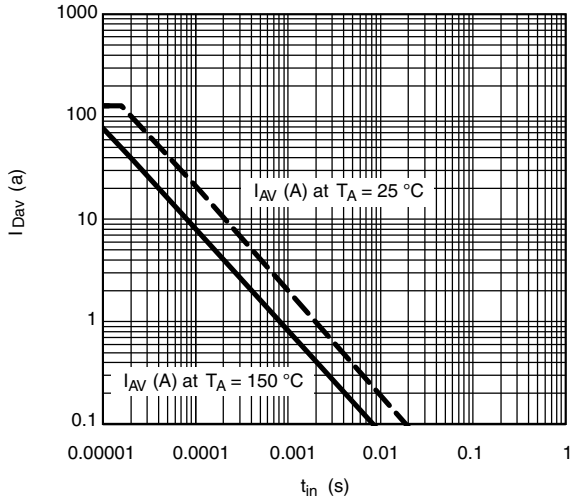
TYPICAL CHARACTERISTICS (25 °C unless noted)



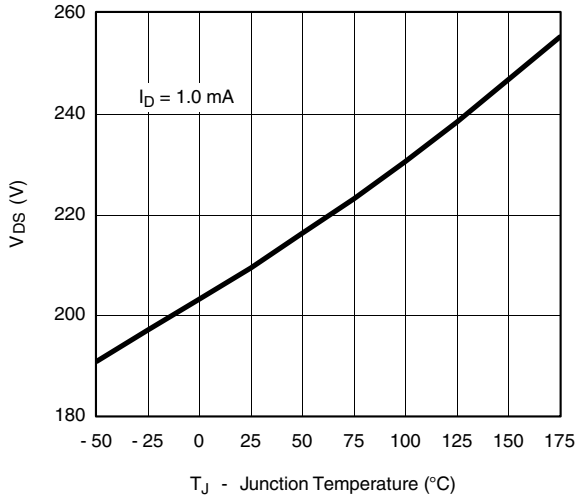
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

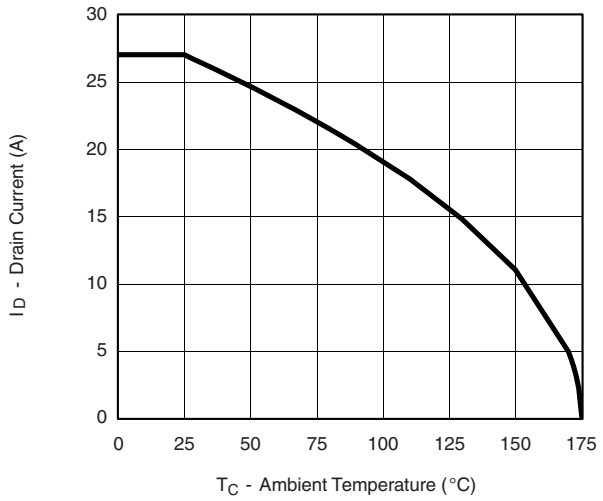


Avalanche Current vs. Time

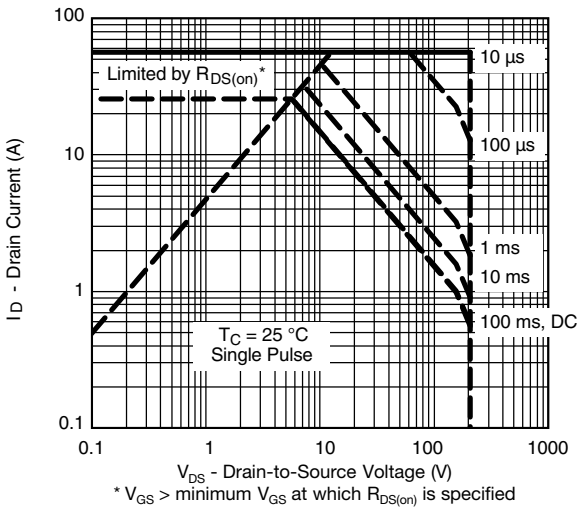


Drain Source Breakdown vs. Junction Temperature

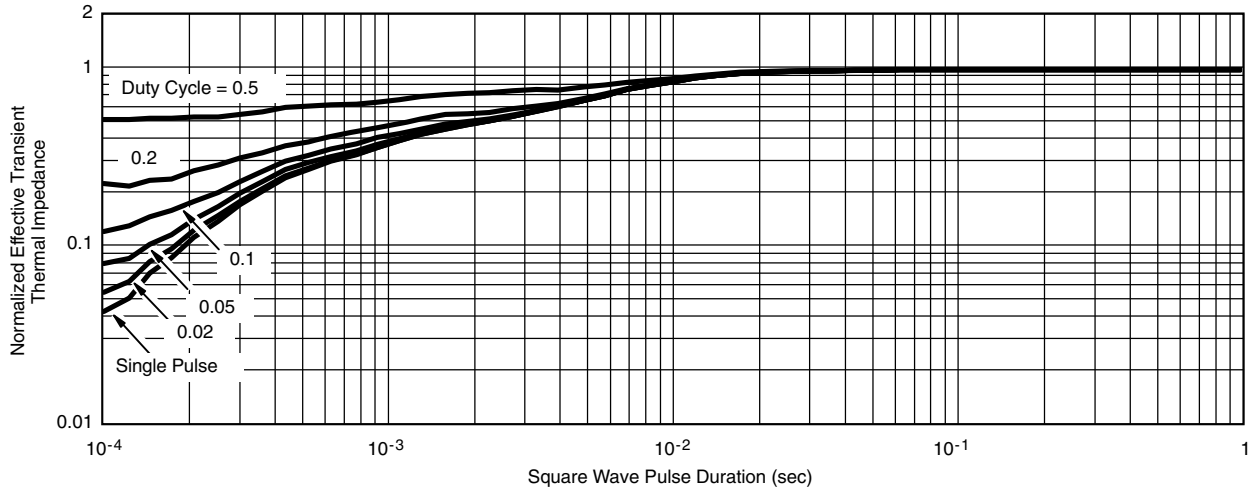
THERMAL RATINGS



Maximum Avalanche and Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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